MODEL KDI350-225G-50R0J
High Power Chip Termination

100 Watts

When properly mounted on an appropriate heat sink, this chip device provides high power dissipation capabilities. Ideal for ferrite isolator applications, the improved thin film design technology and laser trimming provide proven peak and average RF power capabilities to meet the demands of today's CDMA and WCDMA system requirements. Aluminum Nitride is featured for those applications where the use and disposal of Beryllium oxide is a concern.

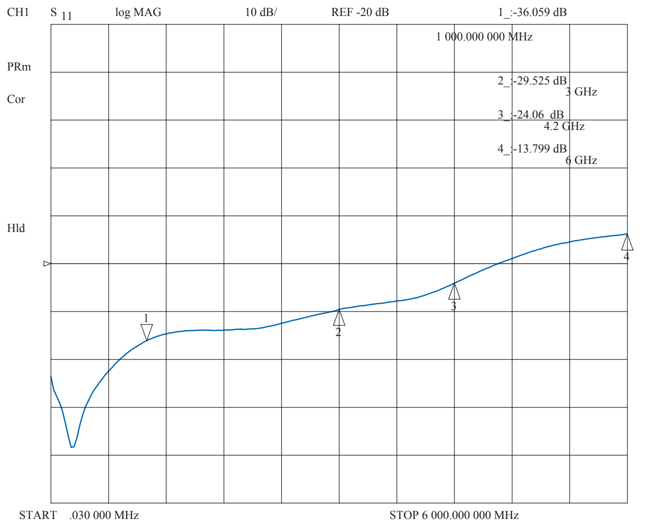
- Environmentally friendly AlN substrate
- Hi-performance, thin film element
- Power Handling of 100 Watts
- New adhesion process results in improved terminal strength
- On-chip matching network improves frequency performance over the DC-3 GHz frequency range

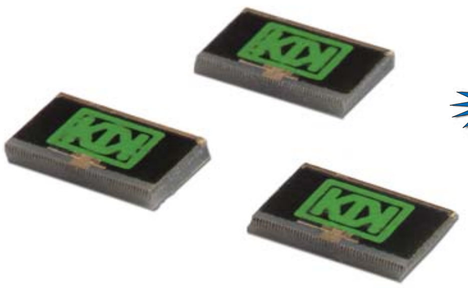
SPECIFICATIONS

Parameters	Specifications
Frequency Range	DC to 3 GHz
Power	100 Watts*
VSWR	1.10:1 max
Resistance	50 ohms +/- 5%
Operating Temperature	-55 °C to 150 °C
Substrate	Aluminum Nitride

* Refer to average power derating curve chart.

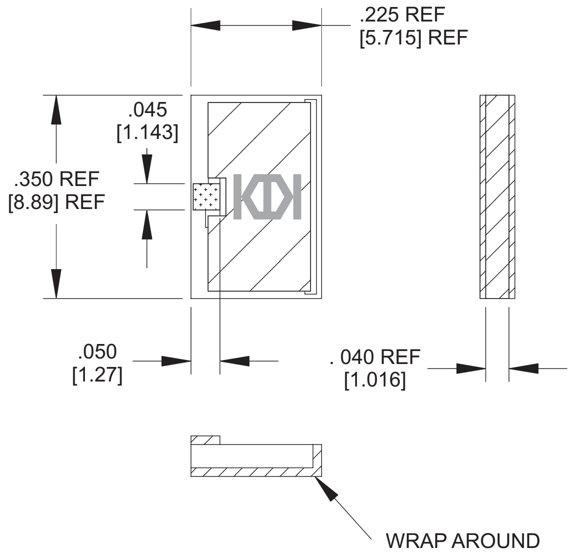
TYPICAL PERFORMANCE





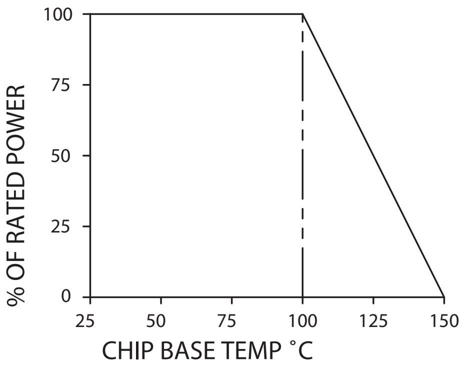
NEW

PHYSICAL DIMENSIONS



NOTE: Dimension are in inches [mm].

AVERAGE POWER DERATING CURVE



ISO 9001 REGISTERED FIRM